

WSR80P06

P-Ch MOSFET

General Description

The WSR80P06 uses advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

Features

- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Absolute Maximum Ratings

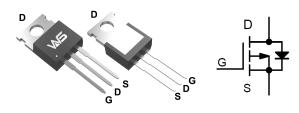
Product Summery

BV _{DSS}	R _{DSON}	I _D
-60V	18mΩ	-50A

Applications

•Battery protection /Load switch /Uninterruptible power supply

TO-220AB Pin Configuration



Symbol Parameter Rating Units V Drain-Source Voltage -60 V_{DS} v Gate-Source Voltage V_{GS} ± 20 -50 А Continuous Drain Current, V_{GS} @ -10V;T_C=25°C I_D -34 Continuous Drain Current, V_{GS} @ -10V;T_C=100°C А ls **Diode Continuous Forward Current** -20 А 45 I_{AS} Avalanche Energy, Single pulse ;L=1mH А 101 mJ E_{AS} Avalanche Energy, Single pulse;;L=1mH Pulse Drain Current Tested ;Tc=25°C -90 I_{DP} А Maximum Power Dissipation;T_C=25°C 86.8 W P_D 35 W Maximum Power Dissipation;T_C=100°C -55 to 150 °C T_{STG} Storage Temperature Range °C ТJ **Operating Junction Temperature Range** -55 to 150

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit	
R _{θJA}	Thermal Resistance Junction-Ambient ¹		62	°C/W	
R _{θJC}	Thermal Resistance Junction-Case ¹		1.44	℃/W	



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Electrical Characteristics (T_J=25 [°]C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-60			V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-18A		13	18	mΩ
		V _{GS} =-4.5V , I _D =-12A		18	25	
V _{GS(th)}	Gate Threshold Voltage	V_{GS} = V_{DS} , I_D =-250 uA	-1.3		-3.0	V
_	Drain-Source Leakage Current	V_{DS} =-48V , V_{GS} =0V , T _J =25 $^\circ C$			1	uA
I _{DSS}		V_{DS} =-48V , V_{GS} =0V , T _J =55 $^\circ$ C			5	
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm20V$, V_{DS} =0V			±100	nA
gfs	Forward Transconductance	V _{DS} =-10V , I _D =-18A		23		S
Qg	Total Gate Charge (-4.5V)	V _{DS} =-20V , V _{GS} =-4.5V , I _D =-12A		25		
Q _{gs}	Gate-Source Charge			6.7		nC
Q _{gd}	Gate-Drain Charge			5.5		
T _{d(on)}	Turn-On Delay Time			38		
Tr	Rise Time	V _{DD} =-15V , V _{GS} =-10V ,		23.6		ns
T _{d(off)}	Turn-Off Delay Time	R _G =3.3Ω, I _D =-1A		100		
T _f	Fall Time			6.8		
C _{iss}	Input Capacitance			3635		
Coss	Output Capacitance	V _{DS} =-15V , V _{GS} =0V , f=1MHz		224		pF
C _{rss}	Reverse Transfer Capacitance			141		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
V _{SD}	Diode Forward Voltage ²	V_{GS} =0V , I_{S} =-1A , T_{J} =25 $^{\circ}$ C			-1.2	V

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%

3. The EAS data shows Max. rating . The test condition is V_{DD} =-25V, V_{GS} =-10V, L=0.1mH, I_{AS} =-45A

4.The power dissipation is limited by 150°C junction temperature

5. The data is theoretically the same as I_{D} and I_{DM} , in real applications , should be limited by total power dissipation.



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Typical Characteristics

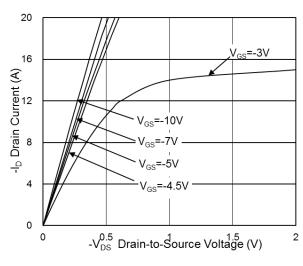


Fig.1 Typical Output Characteristics

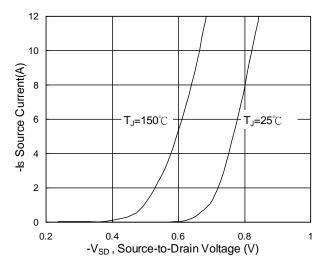
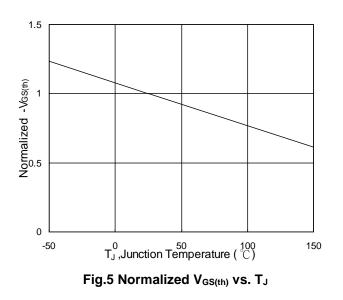


Fig.3 Source Drain Forward Characteristics



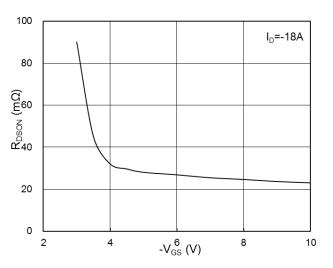


Fig.2 On-Resistance vs. G-S Voltage

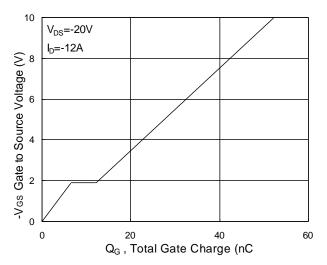


Fig.4 Gate-Charge Characteristics

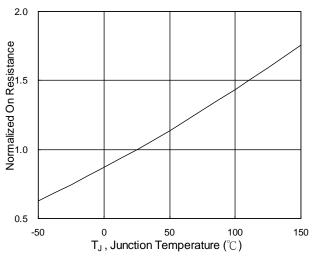


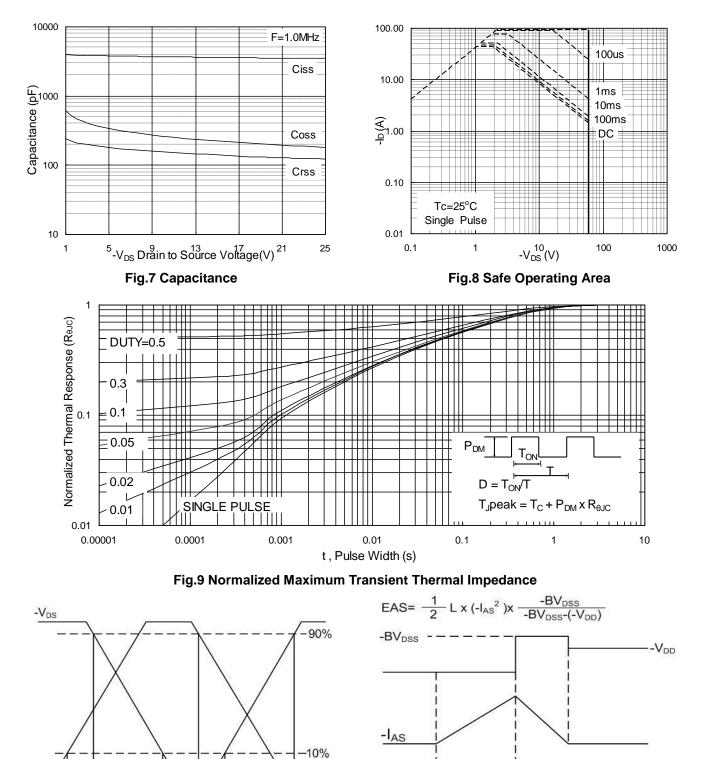
Fig.6 Normalized R_{DSON} vs. T_J



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Typical Characteristics



-V_{GS}

 $-V_{GS}$



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